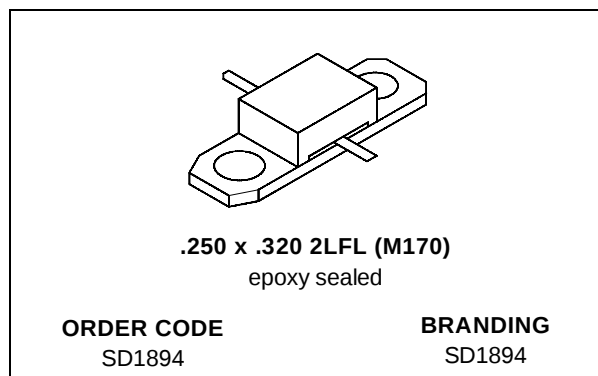


RF & MICROWAVE TRANSISTORS SATELLITE COMMUNICATIONS APPLICATIONS

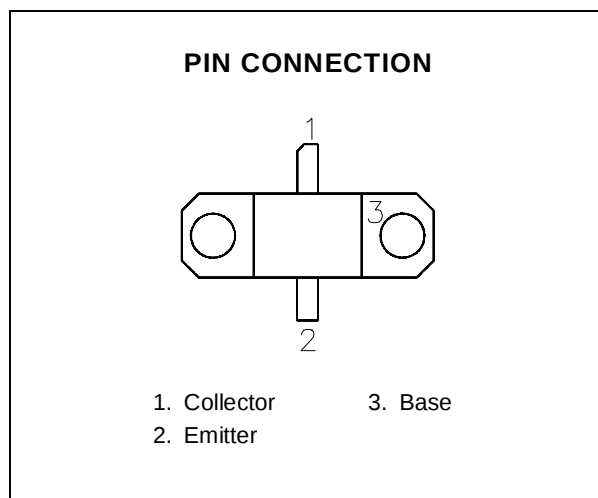
- CLASS C
- 1.6 GHz
- COMMON BASE
- REFRACTORY/GOLD METALLIZATION
- EFFICIENCY = 50% MIN.
- $P_{OUT} = 4.5 \text{ W MIN. WITH } 10 \text{ dB GAIN}$



DESCRIPTION

The SD1894 is a common base silicon NPN bipolar device optimized for 1.6 GHz SATCOM applications.

The SD1894 offers superior gain and collector efficiency, making it an ideal choice for Class C power amplifiers used in portable as well as fixed SATCOM terminals.



ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	45	V
V_{CES}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	3.0	V
I_C	Device Current	375	mA
P_{DISS}	Power Dissipation	12.5	W
T_J	Junction Temperature	+200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	- 65 to +150	$^{\circ}\text{C}$

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	14.0	$^{\circ}\text{C/W}$
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ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

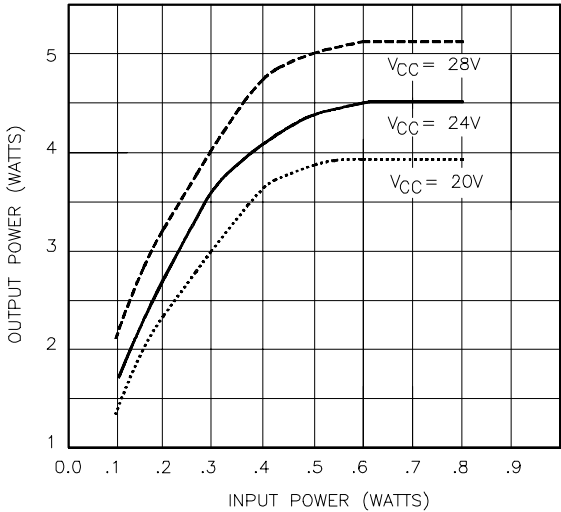
STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV _{CBO}	I _C = 1 mA	I _E = 0 mA	45	—	—	V
BV _{CES}	I _C = 1 mA	V _{BE} = 0 V	45	—	—	V
BV _{EBO}	I _E = 1 mA	I _C = 0 mA	3.0	—	—	V
I _{CBO}	V _{CB} = 28 V	I _E = 0 mA	—	—	.25	mA
h _{FE}	V _{CE} = 5 V	I _C = .2 A	15	—	150	—

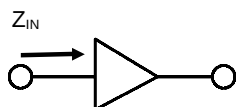
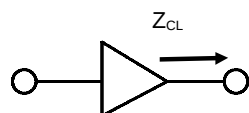
DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P _{IN}	f = 1650 MHz	V _{CC} = 28 V	P _{OUT} = 4.5 W	—	.35	.45	W
η _C	f = 1650 MHz	V _{CC} = 28 V	P _{OUT} = 4.5 W	50	55	—	%
P _G	f = 1650 MHz	V _{CC} = 28 V	P _{OUT} = 4.5 W	10.0	11.1	—	dB
Load Mismatch	V _{CC} = 28 V	P _{OUT} = 4.5 W	VSWR = 20:1	No Degradation in Output Power			

INPUT POWER vs OUTPUT POWER

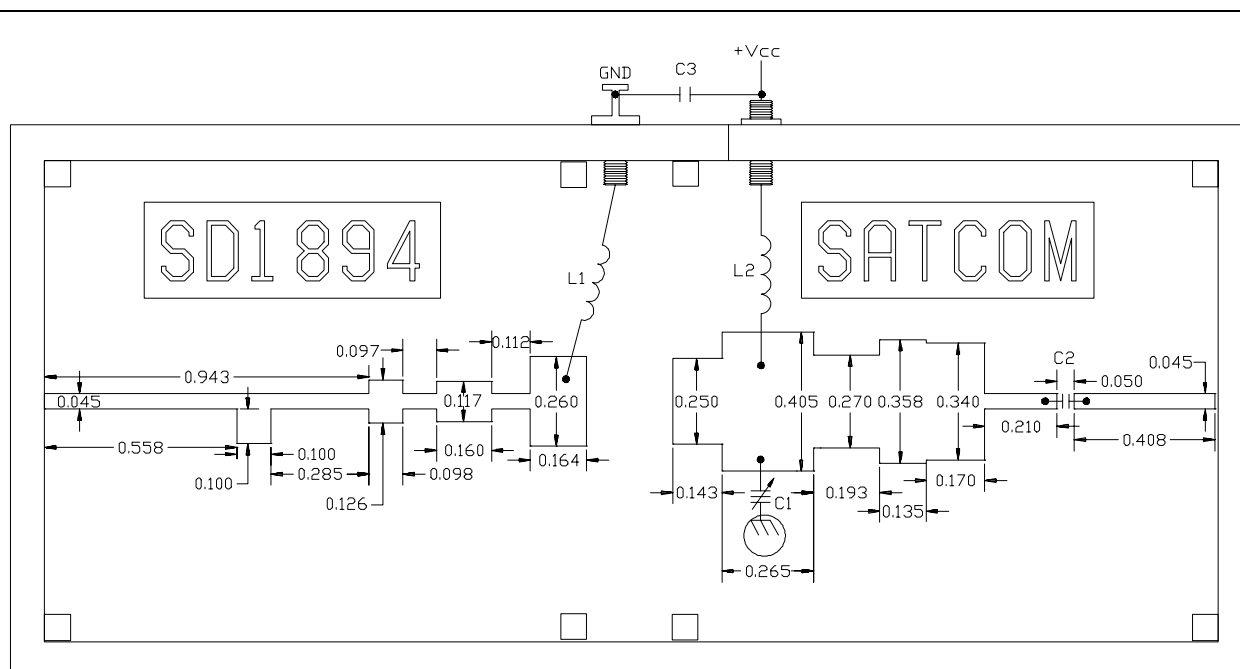


IMPEDANCE DATA

TYPICAL INPUT
IMPEDANCETYPICAL COLLECTOR LOAD
IMPEDANCE

FREQ.	$Z_{IN} (\Omega)$	$Z_{CL} (\Omega)$
1600 MHz	$31.6 + j 21.4$	$5.2 + j 14.7$
1620 MHz	$38.0 + j 15.0$	$5.6 + j 14.55$
1635 MHz	$38.8 + j 11.3$	$5.85 + j 14.45$
1650 MHz	$36.0 + j 9.1$	$6.1 + j 14.3$
1665 MHz	$34.3 + j 8.77$	$6.37 + j 14.2$

TEST CIRCUIT



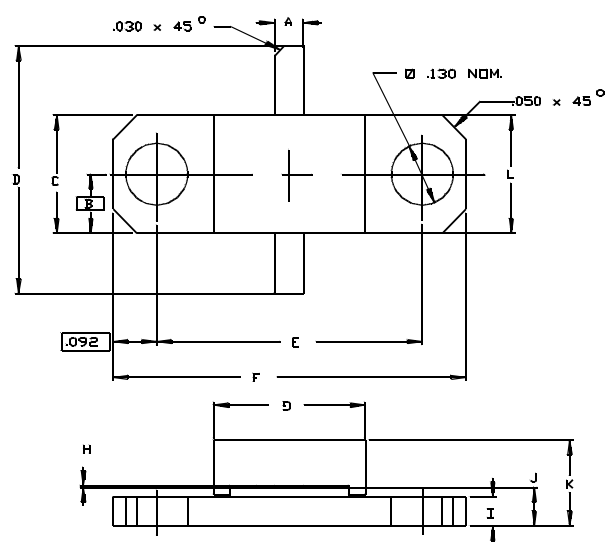
C1: .6 - 4.5 pf Johanson
 C2: 39pf ATC Chip Capacitor
 C3: .1 μ f Ceramic

L1 : 10 Turns, AWG #28, .080" I.D.
 L2 : 4 Turns, AWG #28, .080" I.D.

Board Material: Er = 10.2, Thickness .050"

PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0170
UDCS No. 1010996 rev B



SGS-THOMSON MICROELECTRONICS			CONT'D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.055/1,40	.065/1,65	K		.190/4,83
B	.124/3,15		L	.245/6,22	.255/6,48
C	.243/6,17	.253/6,43			
D	.635/16,13	.665/16,89			
E	.555/14,10	.565/14,35			
F	.739/18,77	.749/19,02			
G	.315/8,00	.325/8,26			
H	.002/0,05	.006/0,15			
I	.055/1,40	.065/1,65			
J	.075/1,91	.095/2,41			

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